

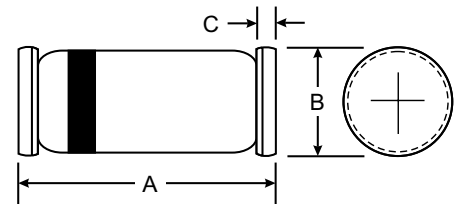


### Features

- Fast Switching Speed
- General Purpose Rectification
- Silicon Epitaxial Planar Construction

### Mechanical Data

- Case: SOD-80/LL34, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



LL34/ SOD-80		
Dim	Min	Max
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Sym	Parameter	Value	Units
$T_{stg}$	Storage Temperature	-65 to +200	$^\circ\text{C}$
$T_J$	Operating Junction Temperature	-65 to +200	$^\circ\text{C}$
$P_D$	Total Power Dissipation at $T_A = 25^\circ\text{C}$	500	mW
	Linear Derating Factor from $T_A = 25^\circ\text{C}$	3.33	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	350	$^\circ\text{C}/\text{W}$
$W_{iv}$	Working Inverse Voltage	180	V
$I_O$	Average Rectified Current	200	mA
$I_F$	DC Forward Current ( $I_F$ )	500	mA
$i_f$	Recurrent Peak Forward Current	600	mA
$i_{F(surge)}$	Peak Forward Surge Current (IFSM) Pulse Width = 1.0 second	1.0	Amp
	Pulse Width = 1.0 microsecond	4.0	Amp

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

### Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
$B_V$	Breakdown Voltage	200		V	$I_R = 100 \mu\text{A}$
$I_R$	Reverse Leakage		25 5.0	nA $\mu\text{A}$	$V_R = 180 \text{ V}$ $V_R = 180 \text{ V } T_A = 150^\circ\text{C}$
$V_F$	Forward Voltage		1.00	V	$I_F = 100 \text{ mA}$
$C_T$	Capacitance		6.0	pF	$V_R = 0.0 \text{ V}, f = 1.0 \text{ MHz}$